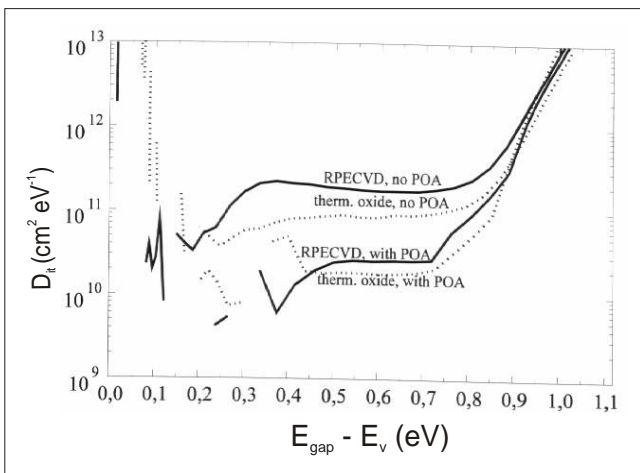
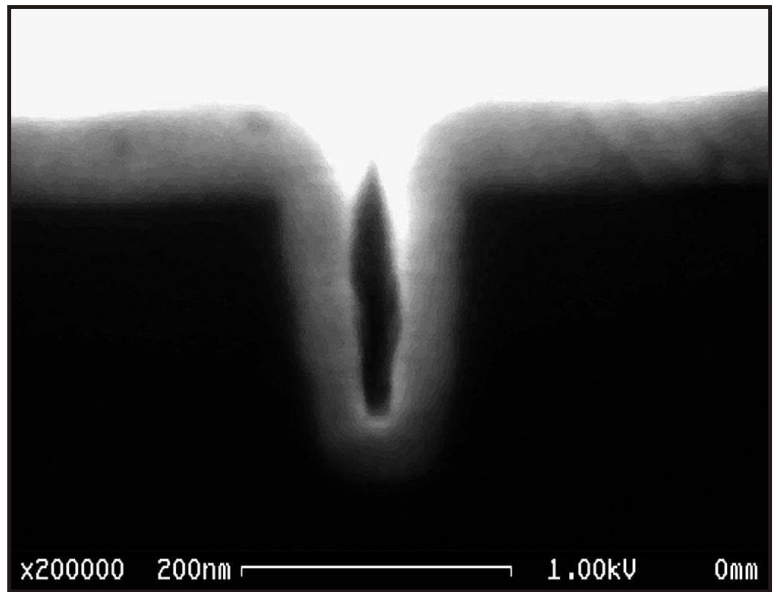
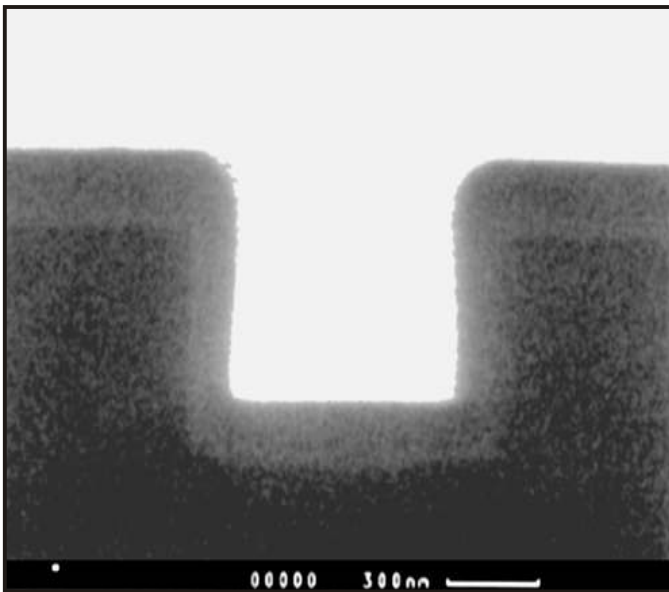




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# Plasmalab Data

## Very High Quality PECVD SiO<sub>2</sub> by ICP

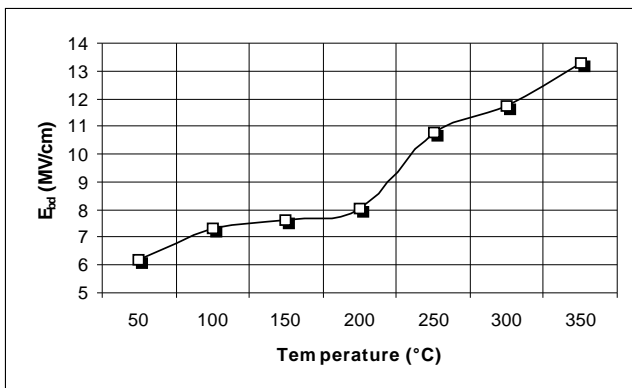


Courtesy of the RWTH Aachen Institut für Halbleitertechnik II, Prof. Kurz  
 Contact J. Stein

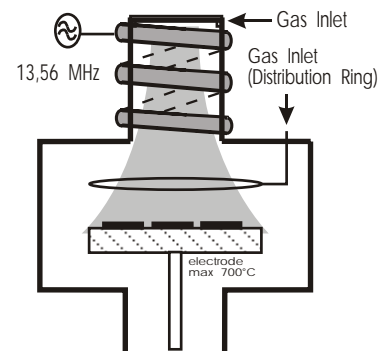
SEM's show the conformal deposition of 0.2 μm / 0.07 μm SiO<sub>2</sub>  
 rate: 5 - 20 nm/ min  
 uniformity over one wafer: +/- 4 %

Distribution of the interface state density  $D_{it}$  inside the band gap:  
 remote PECVD SiO<sub>2</sub> vs thermal SiO<sub>2</sub>  
 Post Anneal (POA) at 1050° C, 25 min N<sub>2</sub>

- Plasmalab 80 Plus*
- Plasmalab System 100*
- Plasmalab System 133*



Electrical Breakdown Field vs Deposition Temperature



Plasma Enhanced Chemical Vapour Deposition with (remote) Inductive Coupled Plasma source